

SANYO	No.3701A	<h1 style="margin: 0;">2SC4632</h1> <p style="margin: 0;">NPN Triple Diffused Planar Silicon Transistor</p> <p style="margin: 0;">High-Voltage Amp, High-Voltage Switching Applications</p>
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Features

- High breakdown voltage ($V_{CEO \text{ min}} = 1200V$).
- Small Cob (typical Cob = 1.6pF).
- Full-isolation package.
- High reliability (Adoption of HVP process).

Absolute Maximum Ratings at $T_a = 25^\circ C$

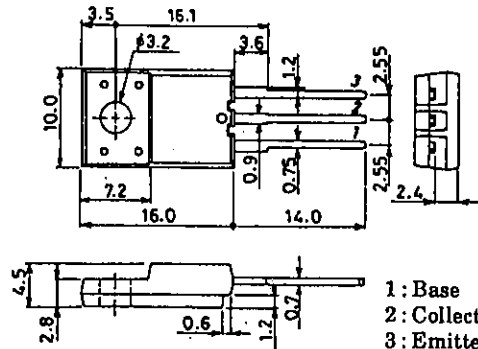
			unit
Collector-to-Base Voltage	V_{CBO}	1500	V
Collector-to-Emitter Voltage	V_{CEO}	1200	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	10	mA
Collector Current (Pulse)	I_{CP}	30	mA
Collector Dissipation	P_C	2	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 1200V, I_E = 0$			1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$			1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 0.5mA$	10		60	
Gain-Bandwidth Product	f_T	$V_{CE} = 10V, I_C = 0.5mA$		6		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 1mA, I_B = 0.2mA$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 1mA, I_B = 0.2mA$			2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	1500			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	1200			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5			V
Output Capacitance	Cob	$V_{CB} = 100V, f = 1MHz$		1.6		pF
Thermal Resistance	R_{thj-c}	Junction - case			12.5	$^\circ C/W$

Package Dimensions 2079B

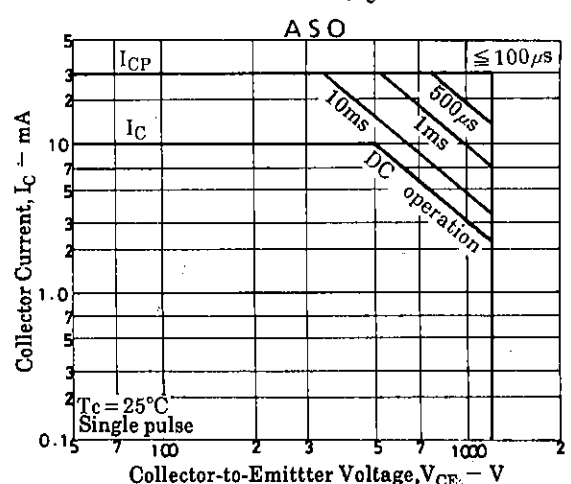
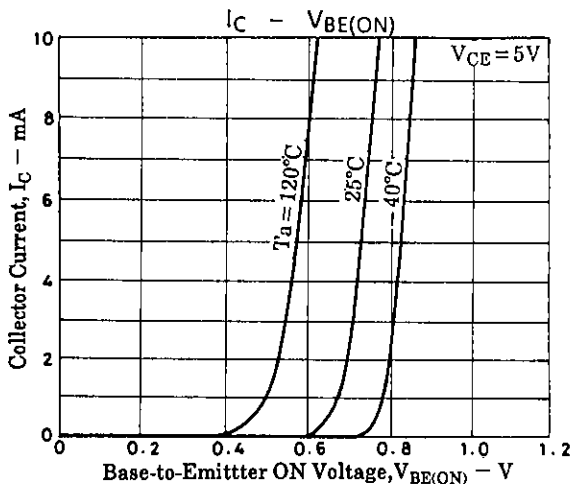
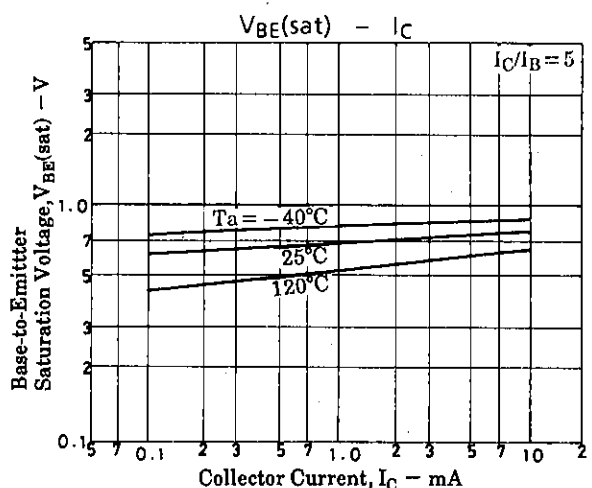
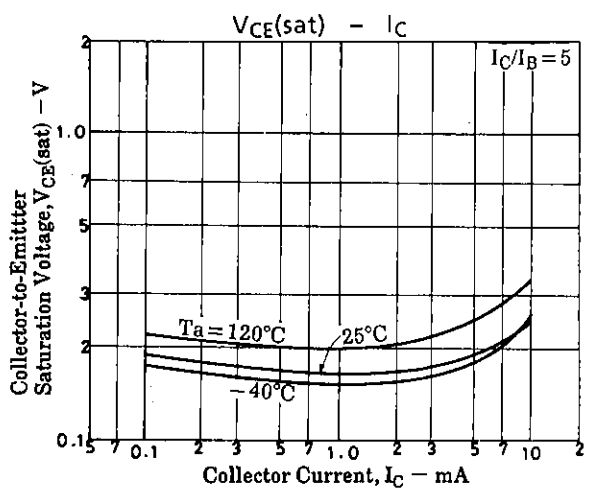
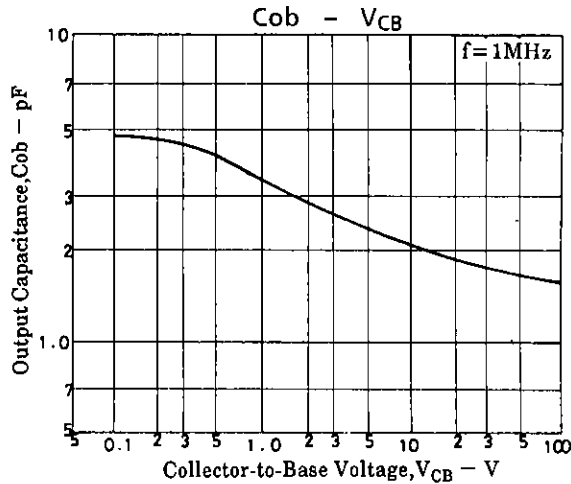
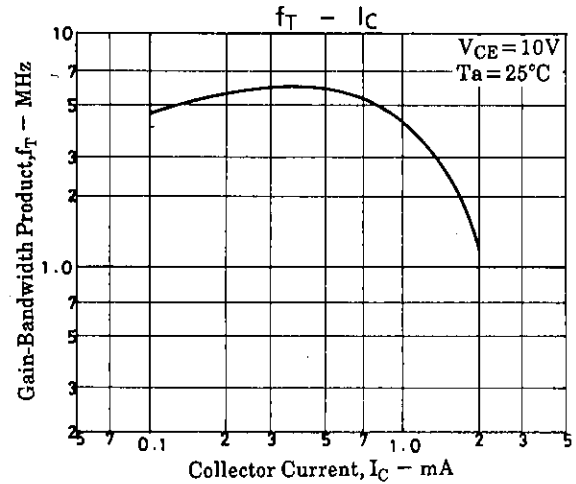
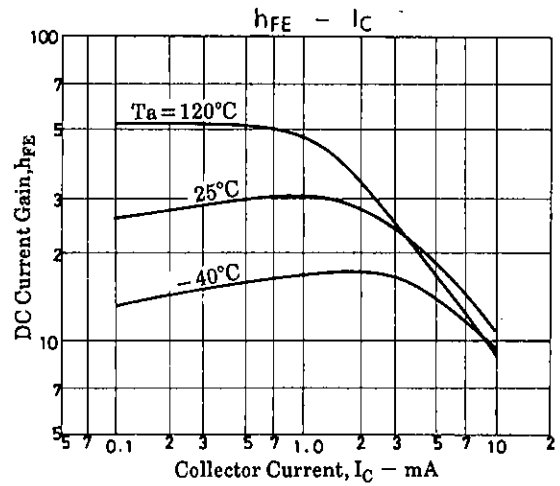
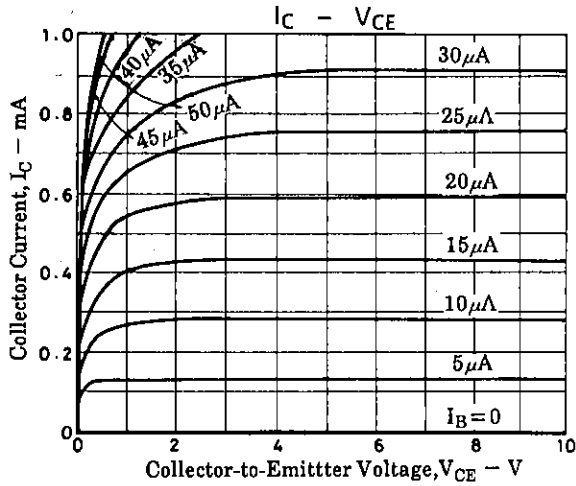
(unit : mm)

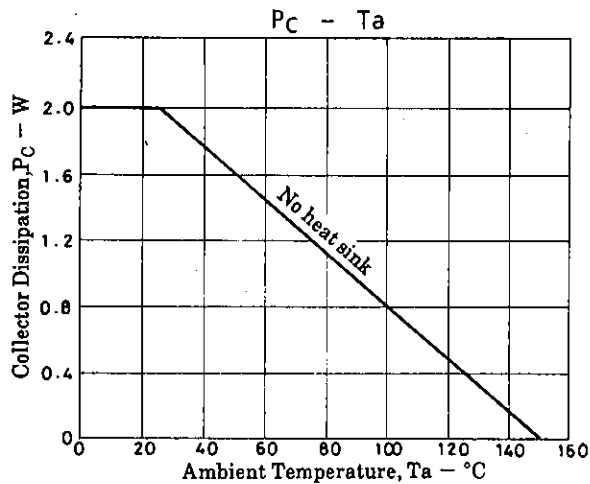


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